



## 10N100-FC

Power MOSFET

### 10A, 1000V N-CHANNEL POWER MOSFET

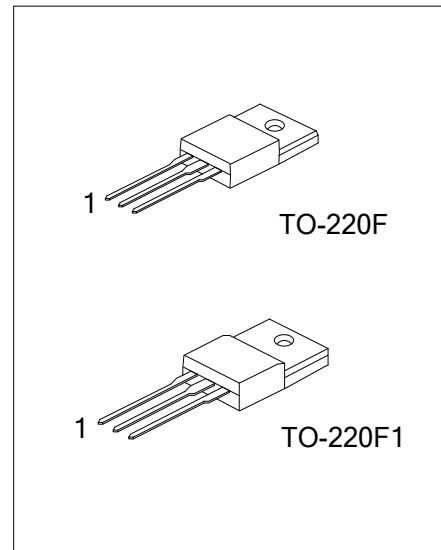
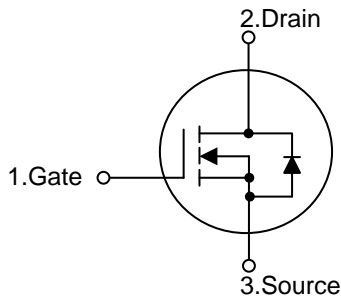
#### DESCRIPTION

The UTC 10N100-FC provide excellent  $R_{DS(ON)}$ , low gate charge and operation with low gate voltages. This device is suitable for use as a load switch or in PWM applications.

#### FEATURES

- \*  $R_{DS(ON)} \leq 1.4\Omega$  @  $V_{GS}=10V, I_D=5.0A$
- \* Low Reverse Transfer Capacitance
- \* Fast Switching Capability
- \* Avalanche Energy Specified
- \* Improved  $dv/dt$  Capability, High Ruggedness

#### SYMBOL



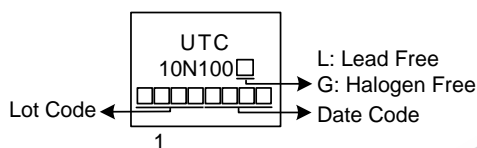
#### ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
10N100L-TF1-T	10N100G-TF1-T	TO-220F1	G	D	S	Tube
10N100L-TF3-T	10N100G-TF3-T	TO-220F	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>10N100G-TF1-T</p>	<p>(1) T: Tube (2) TF1: TO-220F1, TF3: TO-220F (3) G: Halogen Free and Lead Free, L: Lead Free</p>
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#### MARKING



### ■ ABSOLUTE MAXIMUM RATINGS (T<sub>C</sub> = 25°C, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Drain-Source Voltage	V <sub>DSS</sub>	1000	V
Gate-Source Voltage	V <sub>GSS</sub>	±30	V
Drain Current	Continuous	I <sub>D</sub>	10 A
	Pulsed (Note 2)	I <sub>DM</sub>	20 A
Avalanche Energy	Single Pulsed (Note 3)	E <sub>AS</sub>	92.5 mJ
Peak Diode Recovery dv/dt (Note 4)	dv/dt	2.1	V/ns
Power Dissipation	P <sub>D</sub>	40	W
Junction Temperature	T <sub>J</sub>	+150	°C
Storage Temperature	T <sub>STG</sub>	-55 ~ +150	°C

- Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.  
 2. Repetitive Rating : Pulse width limited by maximum junction temperature.  
 3. L=10mH, I<sub>AS</sub>=4.3A, V<sub>DD</sub>=50V, R<sub>G</sub>=25 Ω, Starting T<sub>J</sub> = 25°C  
 4. I<sub>SD</sub>≤10A, di/dt≤200A/μs, V<sub>DD</sub> ≤ BV<sub>DSS</sub>, Starting T<sub>J</sub> = 25°C

### ■ THERMAL DATA

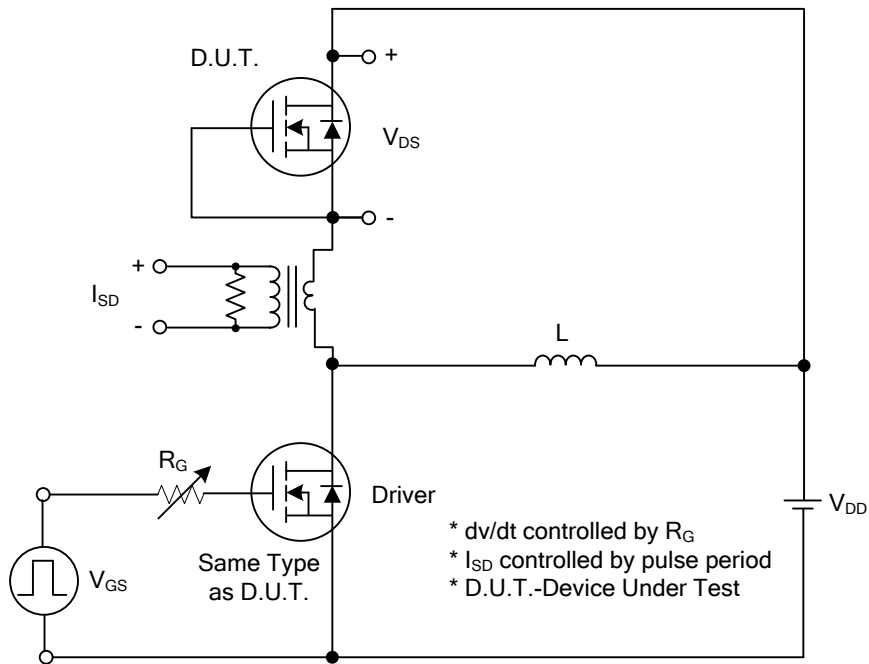
PARAMETER	SYMBOL	RATING	UNIT
Junction to Ambient	θ <sub>JA</sub>	62.5	°C/W
Junction to Case	θ <sub>JC</sub>	3.1	°C/W

### ■ ELECTRICAL CHARACTERISTICS (T<sub>J</sub> =25°C, unless otherwise specified)

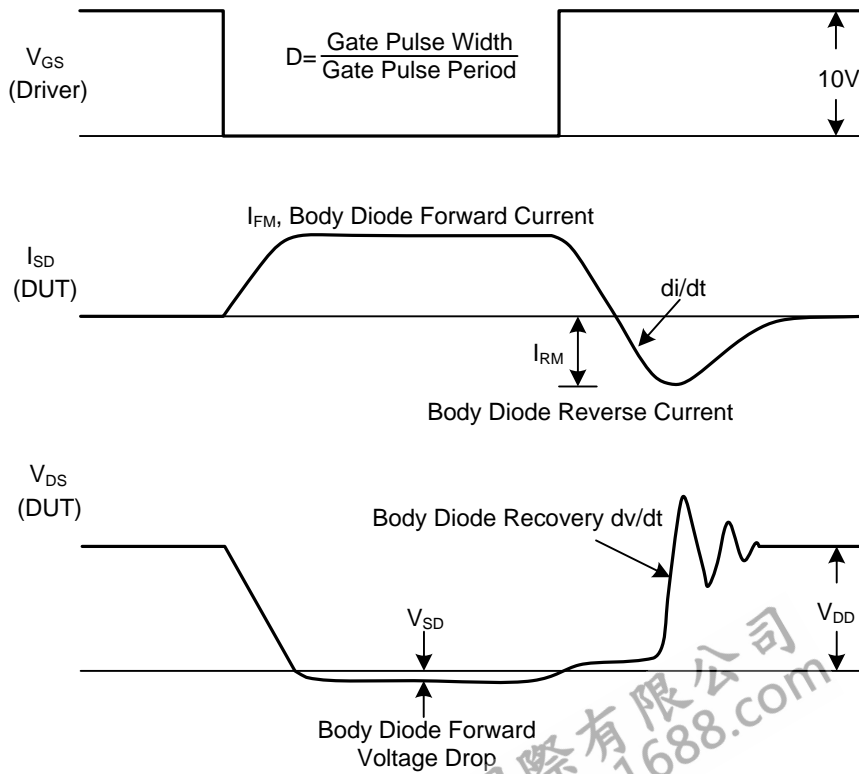
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>OFF CHARACTERISTICS</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	1000			V
Drain-Source Leakage Current	I <sub>DSS</sub>	V <sub>DS</sub> =1000V, V <sub>GS</sub> =0V			10	μA
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±30V, V <sub>DS</sub> =0V			±100	nA
<b>ON CHARACTERISTICS</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	3.0		5.0	V
Static Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =5.0A			1.4	Ω
<b>DYNAMIC CHARACTERISTICS</b>						
Input Capacitance	C <sub>ISS</sub>	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, f=1MHz		2540		pF
Output Capacitance	C <sub>OSS</sub>			190		pF
Reverse Transfer Capacitance	C <sub>RSS</sub>			1		pF
<b>SWITCHING CHARACTERISTICS</b>						
Total Gate Charge (Note 1)	Q <sub>G</sub>	V <sub>DS</sub> =800V, V <sub>GS</sub> =10V, I <sub>D</sub> =10A I <sub>G</sub> =1mA (Note 1, 2)		38		nC
Gate-Source Charge	Q <sub>GS</sub>			14		nC
Gate-Drain Charge	Q <sub>GD</sub>			5		nC
Turn-On Delay Time (Note 1)	t <sub>D(ON)</sub>	V <sub>DD</sub> =100V, V <sub>GS</sub> =10V, I <sub>D</sub> =10A, R <sub>G</sub> =25Ω (Note 1, 2)		42		ns
Turn-On Rise Time	t <sub>R</sub>			19		ns
Turn-Off Delay Time	t <sub>D(OFF)</sub>			94		ns
Turn-Off Fall Time	t <sub>F</sub>			32		ns
<b>SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS</b>						
Maximum Continuous Drain-Source Diode Forward Current	I <sub>S</sub>				10	A
Maximum Pulsed Drain-Source Diode Forward Current	I <sub>SM</sub>				20	A
Drain-Source Diode Forward Voltage (Note 1)	V <sub>SD</sub>	I <sub>S</sub> =10A, V <sub>GS</sub> =0V			1.4	V
Body Diode Reverse Recovery Time (Note 1)	t <sub>rr</sub>	I <sub>S</sub> =10A, V <sub>GS</sub> =0V,		1000		nS
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>	di/dt=100A/μs		10		μC

- Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%.  
 2. Essentially independent of operating temperature.

## TEST CIRCUITS AND WAVEFORMS

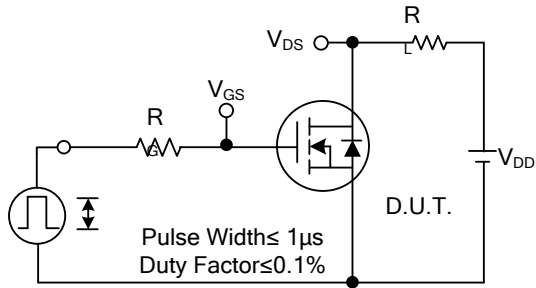


Peak Diode Recovery  $dv/dt$  Test Circuit

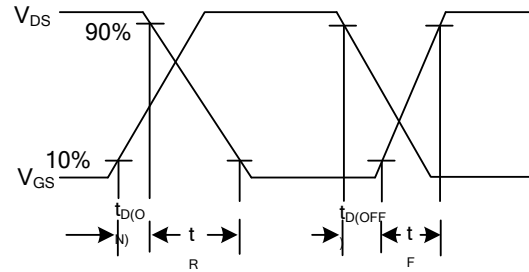


Peak Diode Recovery  $dv/dt$  Waveforms

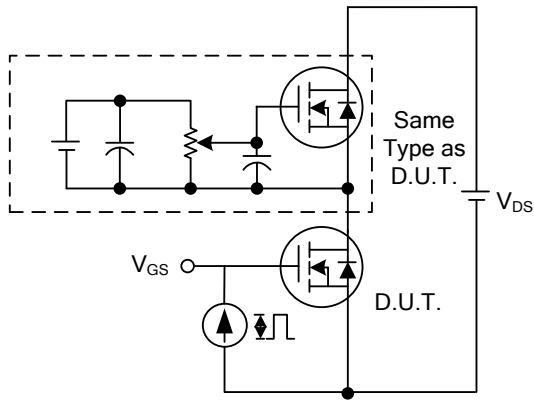
## TEST CIRCUITS AND WAVEFORMS



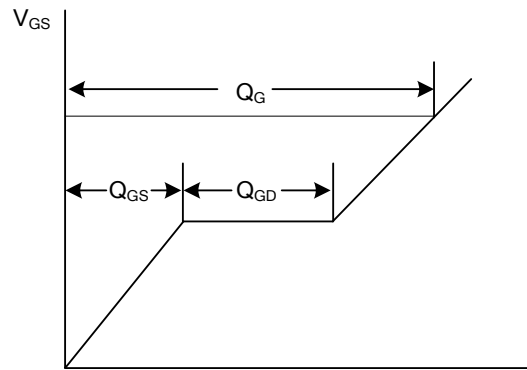
Switching Test Circuit



Switching Waveforms

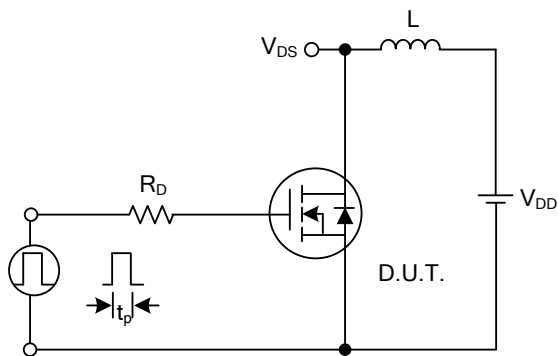


Gate Charge Test Circuit

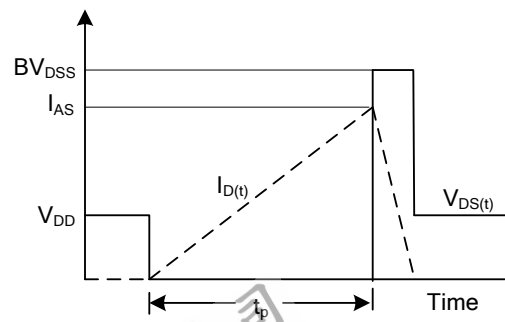


Charge

Gate Charge Waveform

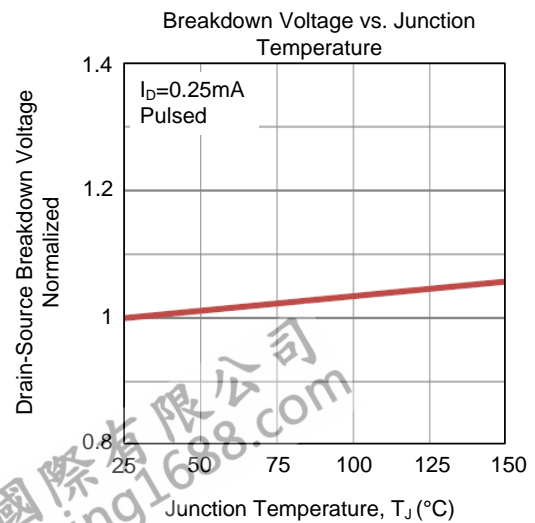
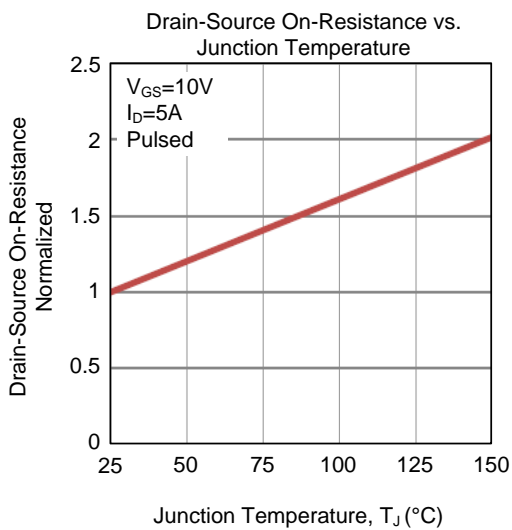
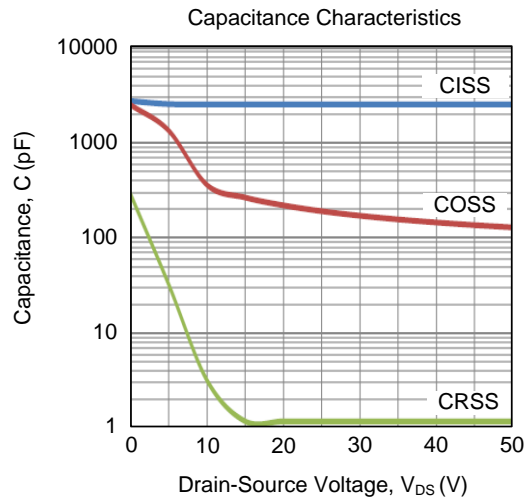
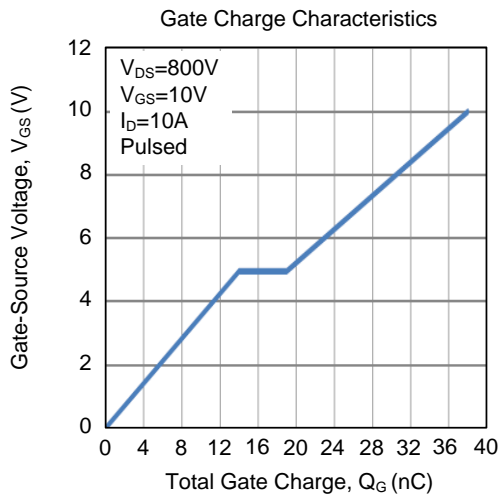
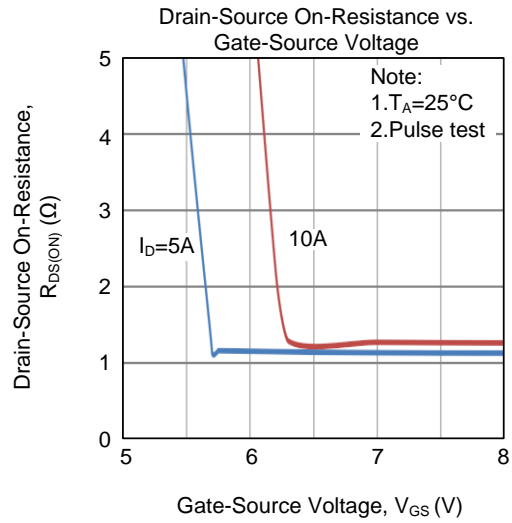
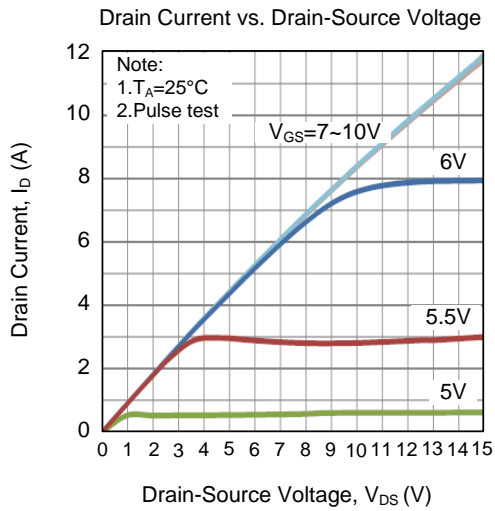


Unclamped Inductive Switching Test Circuit

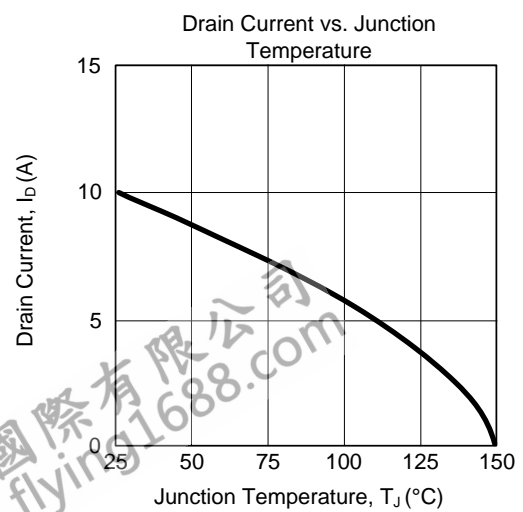
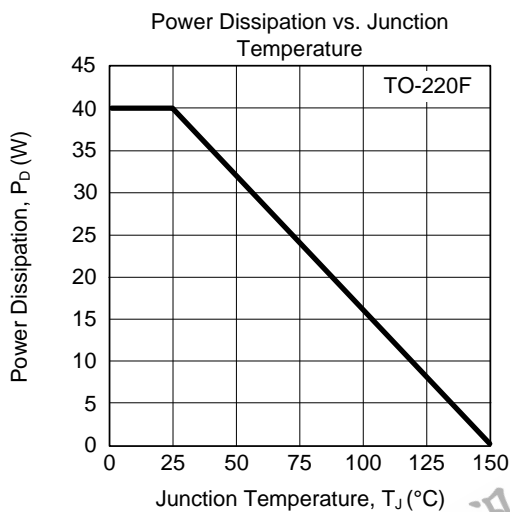
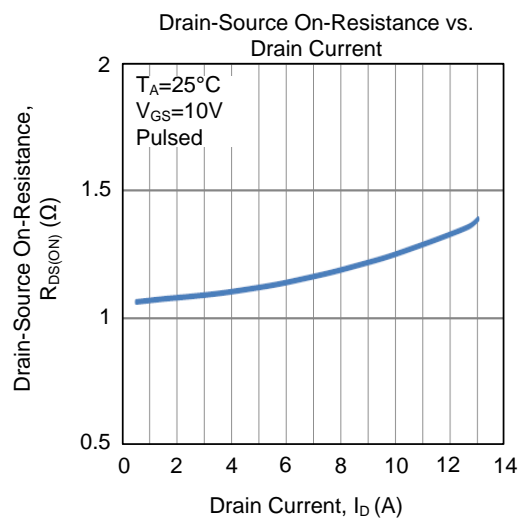
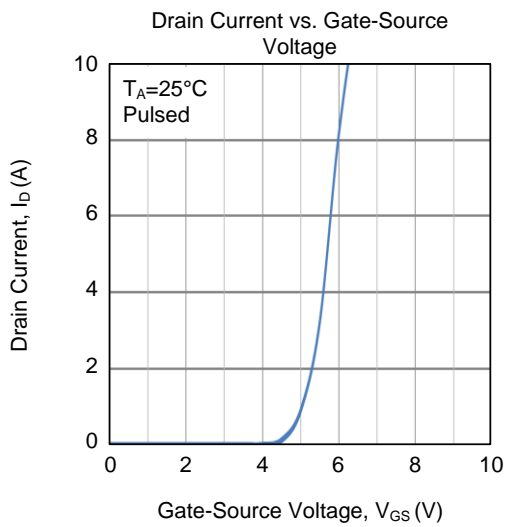
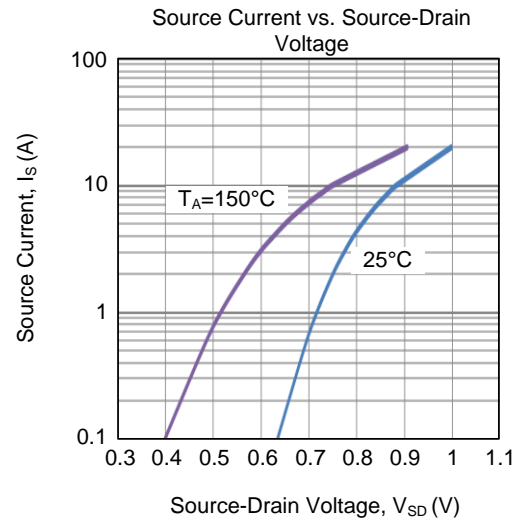
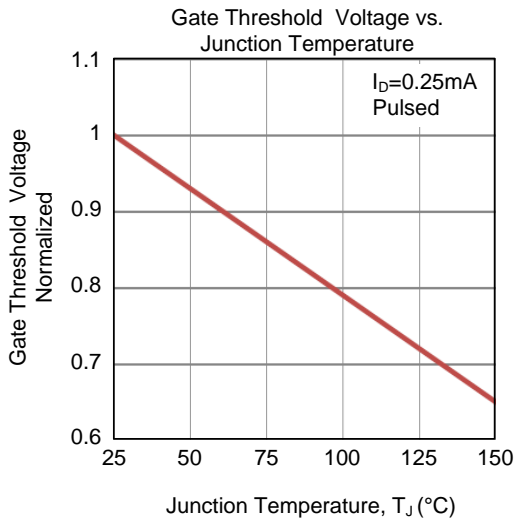


Unclamped Inductive Switching Waveforms

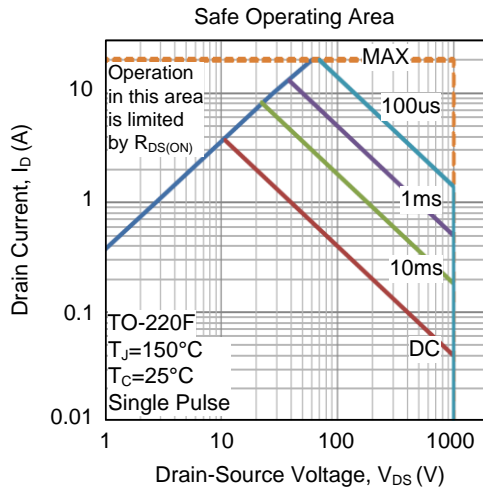
## ■ TYPICAL CHARACTERISTICS



## ■ TYPICAL CHARACTERISTICS (Cont.)



■ TYPICAL CHARACTERISTICS (Cont.)



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